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COMPLETE IF KNOWN 09/018,783 Application Number obite for form 1449A/PTO 1242 INFORMATION DISCLOSURE Confirmation Number 2/4/98 STATEMENT BY APPLICANT Filing Date Ritzdorf First Named Inventor (use as many sheets as necessary) 2823 Group Art Unit Deven M. Collins Examiner Name 29195.8162US Attorney Docket No. of 1 Sheet U.S. PATENT DOCUMENTS Pages, Cohumns, Linus. Date of Publication of Cated Name of Patentee or Applicant Where Relevant Passages or U.S. Patera Document *EXAMINER of Cited Document Kand Code Relevant Figures Appear NUMBER Document MITTALS ((Ciremon) 10/26/99 Dubin et al. Dre AA 5,972,192 2/10/81 Miles et al. AB 4,250,004 7/15/75 Corby et al AC 3,894,918 6/22/48 Allan E. Chester ΑĐ 2,443,599 2/25/97 AE Goolsby et al. 5,605,615 8/28/01 ΑF Mayur et al. 6,280,183 8/21/01 AG 6,278,089 Young et al. FOREIGN PATENT DOCUMENTS Pages, Columns, Lines, Where Date of Publication of Foreign Patent Document Name of Palentes or Applicant -KYAMINER Relevant Passages of Relevant Kind Code of Cited Docum Cited Document No. Figures Apport INITIALS Office (if known) OTHER PRIOR ART-NON PATENT LITERATURE DOCUMENTS include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, EXAMINER journal, scrial, symposium, ostalog, etc.), date, page(s), volumeDissue number(s), publisher, city and/or country where published INITIALS NGUYEN et al, "Interconnect and Contact Metallization", Eds. H.S. Rathore, G.S. Mathan, C. Plougonver and C.C. Schuckert, PV 97-31, The Electrochemical Society. Inc., Pennington, NJ, September HA FOULKE. D.G., in "Gold Plating Technology", Reid, F.H. and Goldie, W., p.67, Electrochemical Publication Limited, British Isles (1996). ΑĬ TOMOV, V., STOYCHEV, D.S., VITANOVA, I.B., "Recovery And Recrystallization Of Electrodeposited Bright Copper Coatings At Room Temperature. II. X-Ray Investigation Of Primary Recrystallization,", Journal of Applied Electrochemistry, 15, 887-894. Chapman and Hall Ltd. (1985). RITZDORF, T., GRAHAM, L., JIN, S., MU, C. and FRASER, D., "Self-Annealing of Electrochemically Deposited Copper Films in Advanced Interconnect Applications," Proceedings of the IEEE 1998 International Interconnect Technology Conference. San Francisco, CA (June 1-3, 1998). DUBIN, V.M., SHACHAM-DIAMAND, Y., ZHAO, B., VASUDEV, P.K. and TING, C.H., "Sub-Half Micror Electroless Cu Metallization," Materials Research Society Symposium Proceedings, Vol. 427, San Francisco AI. (1996).COOK, M. and RICHARDS, T., "The Self-Annealing of Copper," J. Inst. Metals, vol. LXX, pp. 159-173 (1943). AM